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Applicants: Nayfeh et al.

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SILICON NANOPARTICLES AND  
METHOD FOR PRODUCING THE  
SAME

Art Unit: 1754

Examiner: Unassigned

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INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In accordance with 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants through  
counsel submit copies of the patents and publications identified in the attached form PTO-  
1449 as follows:

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#### **OTHER DOCUMENTS**

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U.S. Patent Application Nayfeh et al., Serial number 09/781,147, entitled SILICON NANOPARTICLE ELECTRONIC SWITCHES, filed on February 9, 2001;

U.S. Patent Application Nayfeh et al., Serial number 09/572,121 entitled SILICON NANOPARTICLE MICROCRYSTAL NONLINEAR OPTICAL DEVICES, filed on May 17, 2000;

U.S. Patent Application Nayfeh et al., Serial number 09/496,506 entitled SILICON NANOPARTICLE FIELD EFFECT TRANSISTOR AND TRANSISTOR MEMORY DEVICE, filed on February 2, 2000; and

U.S. Patent Application Nayfeh et al., Serial number 09/426,204 entitled SILICON NANOPARTICLE STIMULATED EMISSION DEVICES, filed on October 25, 1999.

REMARKS

Applicant respectfully requests that the Examiner consider the above-listed references in the examination of this application and list these references of record in the application.

Respectfully submitted,

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